TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

# 2SK3475

VHF- and UHF-band Amplifier Applications

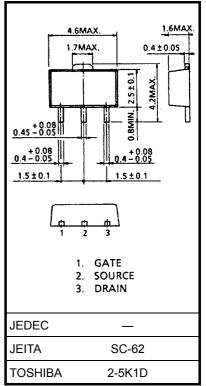
Unit: mm

(Note)The TOSHIBA products listed in this document are intended for high frequency Power Amplifier of telecommunications equipment.These TOSHIBA products are neither intended nor warranted for any other use.Do not use these TOSHIBA products listed in this document except for high frequency Power Amplifier of telecommunications equipment.

- Output power: PO = 630 mW (min)
- Gain: G<sub>P</sub> = 14.9dB (min)
- Drain efficiency:  $\eta_D = 45\%$  (min)

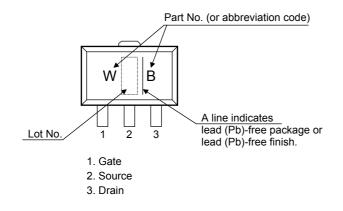
#### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V <sub>DSS</sub>	20	V
Gain-source voltage	V <sub>GSS</sub>	10	V
Drain current	ID	1	А
Power dissipation	P <sub>D</sub> (Note 1)	3	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-45~150	°C



Note 1:  $Tc = 25^{\circ}C$  (When mounted on a 1.6 mm glass epoxy PCB)

#### Marking



Caution: This device is sensitive to electrostatic discharge.

Please make enough tool and equipment earthed when you handle.

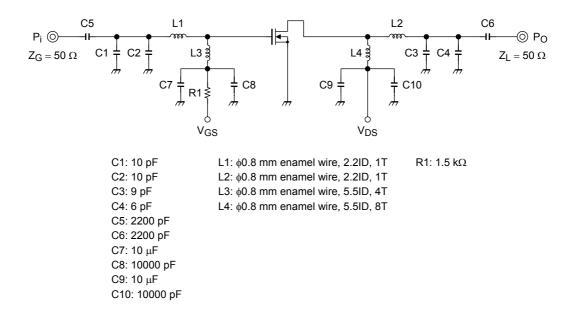
**Electrical Characteristics (Ta = 25°C)** 

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain cut-off current	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_		5	μA
Gate-source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = 10 V	_		5	μA
Threshold voltage	V <sub>th</sub>	$V_{DS} = 7.2 \text{ V}, \text{ I}_{D} = 2 \text{ mA}$	1.9	2.4	2.9	V
Drain-source on-voltage	V <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 75 mA	_	87	_	mV
Forward transconductance	Y <sub>fs</sub>	$V_{DS} = 7.2 \text{ V}, \text{ I}_{DS} = 208 \text{ mA}$	_	260	_	mS
Input capacitance	C <sub>iss</sub>	$V_{DS} = 7.2 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	11	_	pF
Output capacitance	C <sub>oss</sub>	$V_{DS} = 7.2 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	12.5	_	pF
Output power	Po	V <sub>DS</sub> = 7.2 V,	630		_	mW
Drain efficiency	η <sub>D</sub>	$I_{idle} = 50 \text{ mA} (V_{GS} = adjust),$	45			%
Power gain	GP	f = 520 MHz, P <sub>i</sub> = 20 mW,	14.9			dB
Low voltage output power	Pol	V <sub>DS</sub> = 6.0 V, I <sub>idle</sub> = 50 mA (V <sub>GS</sub> = adjust), f = 520 MHz, P <sub>i</sub> = 20 mW,	500	_	_	mW

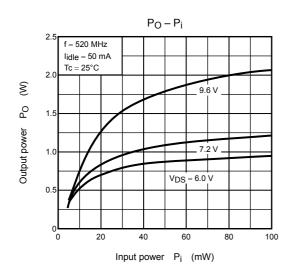
Note 2: These characteristic values are measured using measurement tools specified by Toshiba.

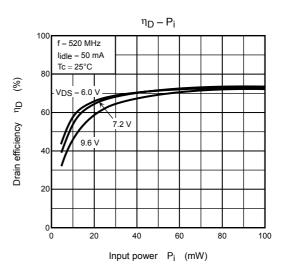
#### Output Power Test Fixture

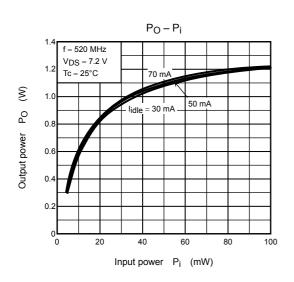
(Test Condition: f = 520 MHz,  $V_{DS}$  = 7.2 V,  $I_{idle}$  = 50 mA,  $P_i$  = 20 mW)

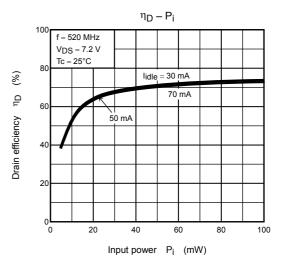


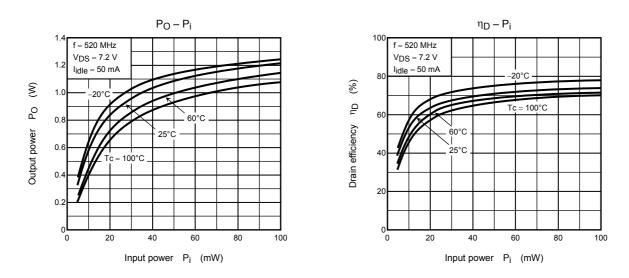
## **TOSHIBA**











Note 3: These are only typical curves and devices are not necessarily guaranteed at these curves.

#### **RESTRICTIONS ON PRODUCT USE**

Handbook" etc..

030619EAA

- The information contained herein is subject to change without notice.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
  In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability
- The TOSHIBA products listed in this document are intended for high frequency Power Amplifier of telecommunications equipment. These TOSHIBA products are neither intended nor warranted for any other use. Do not use these TOSHIBA products listed in this document except for high frequency Power Amplifier of telecommunications equipment.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- TOSHIBA products should not be embedded to the downstream products which are prohibited to be produced and sold, under any law and regulations.

### **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for RF MOSFET Transistors category:

Click to view products by Toshiba manufacturer:

Other Similar products are found below :

FH2164 BLF245 ARF465BG VRF151MP MRF6S20010GNR1 DU28200M VRF2933MP VRF141 MMRF1015NR1 MW6S010GNR1 DU2820S MRF24301HR5 ARF463BP1G ARF465AG MMRF1014NT1 MRF422 VRF161MP ARF468BG MAPHST0045 A2T27S020NR1 UF2840P DU2860U VRF152GMP MRFE6VP5300NR1 BF2040E6814HTSA1 MRFE6VP5150NR1 MMRF5014HR5 LET9060S MRF175GV AFT27S010NT1 AFT27S006NT1 BF999E6327HTSA1 MRF1K50NR5 UF28150J MRFE6VP5600HR6 MRFX1K80HR5 BF998E6327HTSA1 AFM907NT1 AFT05MS006NT1 AFV10700HR5 MRF492 MRF141 MRF171 MRF172 MRF9045LR1 AFM906NT1 BLF578XR,112 TPM9305PD6 CJU02N65 FDS9926A